CHT-IO-1202 PRELIMINARY DATASHEET

## High Temperature 1200V/2A Silicon Carbide Common Cathode Dual Schottky Diode

## General description

CHT-IO-1202 high temperature 1200V/2A Silicon Carbide Common Cathode Dual Schottky Diode is designed to achieve high performance in an extremely wide temperature range: typical operation temperature goes from $-55^{\circ} \mathrm{C}$ to $210^{\circ} \mathrm{C}$ while keeping leakage currents low.
This device is packaged in a hermetically sealed TO-257 metal package especially designed and qualified to sustain high temperature and power cycling. This package offers high voltage isolation between pins and with respect to the case, facilitating the mounting on a heatsink.

The diodes can be used in a variety of applications, including rectification, freewheeling, clamping and general purpose.

## Features

- $\quad$ Specified from $\mathbf{- 5 5}$ to $\mathbf{+ 2 1 0}{ }^{\circ} \mathrm{C}(\mathrm{Tj})$
- Reverse voltage: $\mathrm{V}_{\mathrm{R}}=\mathbf{1 2 0 0 V}$ (max)
- Forward current: $\mathrm{I}_{\mathrm{F}}=2 \mathrm{~A}(\max @$ $210^{\circ} \mathrm{C}(\mathrm{Tj})$ and $\mathrm{V}_{\mathrm{F}}=1.3 \mathrm{~V}$ )
- Forward voltage: $\mathrm{V}_{\mathrm{F}}=1.15 \mathrm{~V}$ (typ.@ $25^{\circ} \mathrm{C}(\mathrm{Tj})$ and $\mathrm{I}_{\mathrm{F}}=2 \mathrm{~A}$ )
- Junction capacitance: $\mathrm{C}_{\mathrm{j}}=11 \mathrm{pF}$ (typ. @ $\mathrm{V}_{\mathrm{R}}=600 \mathrm{~V}$ )
- Hermetically sealed TO-257 metal package
- Pins electrically isolated from the case


## Applications

- Free Wheeling
- Full bridge rectification
- Power supplies
- General purpose diode


## Package Configuration

FRONT VIEW


## 123

TO257 (Pin1 = Cathode; Pin2= Anode 1; Pin3= Anode 2) (case floating)

## Absolute Maximum Ratings

Reverse voltage $\mathrm{V}_{\mathrm{R}}$
Forward surge current $\mathrm{I}_{\text {FSM }}$ Junction temperature $\mathrm{T}_{\mathrm{j}}$

## Operating Conditions

Reverse voltage $\mathrm{V}_{\mathrm{R}} \quad$ OV to 1200 V
Continuous forward current $I_{F}$ 0 A to 2 A 0 V to 2 V Forward voltage $\mathrm{V}_{\mathrm{F}}$ Junction temperature $-55^{\circ} \mathrm{C}$ to $+210^{\circ} \mathrm{C}$

## Electrical characteristics (per diode)

Unless otherwise stated, $T_{j}=25^{\circ} \mathrm{C}$. Bold figures point out values valid over the whole temperature range $\left(T_{j}=-55^{\circ} \mathrm{C}\right.$ to $+210^{\circ} \mathrm{C}$ ).

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Forward voltage | $V_{F}$ | $\mathrm{I}_{\mathrm{F}}=800 \mathrm{~mA}, \mathrm{~T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ |  | 1.15 |  | V |
|  |  | $\mathrm{I}_{\mathrm{F}}=2 \mathrm{~A}, \mathrm{~T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ |  | 1.5 |  | V |
|  |  | $\mathrm{I}_{\mathrm{F}}=800 \mathrm{~mA}, \mathrm{~T}_{\mathrm{j}}=210^{\circ} \mathrm{C}$ |  | 1.3 |  | V |
|  |  | $\mathrm{I}_{\mathrm{F}}=2 \mathrm{~A}, \mathrm{~T}_{\mathrm{j}}=210^{\circ} \mathrm{C}$ |  | 2.18 |  | V |
| Reverse leakage current | $\mathrm{I}_{\mathrm{R}}$ | $\mathrm{V}_{\mathrm{R}}=1200 \mathrm{~V}, \mathrm{~T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ |  | 2 |  | $\mu \mathrm{A}$ |
|  |  | $\mathrm{V}_{\mathrm{R}}=1200 \mathrm{~V}, \mathrm{~T}_{\mathrm{j}}=210^{\circ} \mathrm{C}$ |  | 30 |  | UA |
| Breakdown reverse voltage | $\mathrm{V}_{\text {(BR) }}$ |  | 1200 |  |  | V |
| Junction capacitance | Cj | $\mathrm{V}_{\mathrm{R}}=600 \mathrm{~V}, \mathrm{~T}_{\mathrm{j}}=25^{\circ} \mathrm{C}, \mathrm{f}=100 \mathrm{kHz}$ |  | 10.4 |  | pF |

## Thermal Characteristics

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| Junction-to-Case Thermal re- <br> sistance | $R_{\text {өנc }}$ |  |  | 4.5 |  | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## Typical performances



Figure 1: Diode $\mathrm{I}_{\mathrm{F}}$ vs $\mathrm{V}_{\mathrm{F}}$


Figure 3: Diode $\mathrm{V}_{\mathrm{F}}$ vs Temperature ( $\mathrm{I}_{\mathrm{F}}=800 \mathrm{~mA}$ )


Figure 2: Diode $I_{R}$ vs $V_{R}$


Figure 4:Typical capacitance vs $\mathrm{V}_{\mathrm{R}}$ $\left(\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C} ; \mathrm{f}=100 \mathrm{kHz}, \mathrm{V}_{\mathrm{AC}}=25 \mathrm{mV}\right.$ )

## Package Dimensions



TO257 dimensions in mm (+/- 10\%)

## Ordering Information

| Product Name | Ordering Reference | Package | Marking |
| :---: | :---: | :---: | :---: |
| CHT-IO-1202 | CHT-PLA6609A-TO257-T | TO-257 | CHT-PLA6609A |

## Contact \& Ordering

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